BAS40LT1

Preferred Device

Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Features

Pb–Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	40	V
Forward Power Dissipation @ T _A = 25°C Derate above 25°C	P _F	225 1.8	mW mW/°C
Operating Junction and Storage Temperature Range	$T_{J_1}T_{stg}$	-55 to +150	°C
Forward Continuous Current	I _F	120	mA
	I _{FSM}	200 600	mA
Thermal Resistance Junction-to-Ambient	$R_{ hetaJA}$	508 (Note 1) 311 (Note 2)	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

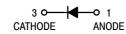
- 1. FR-4 @ minimum pad.
- 2. FR-4 @ 1.0 x 1.0 in pad.



ON Semiconductor®

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40 VOLTS SCHOTTKY BARRIER DIODES





SOT-23 (TO-236AB) CASE 318 STYLE 8

MARKING DIAGRAM



B1 = Specific Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BAS40LT1	SOT-23	3000/Tape & Reel
BAS40LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

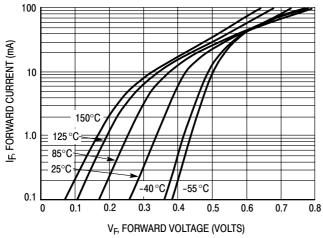
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

BAS40LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage $(I_R = 10 \mu A)$	V _{(BR)R}	40	_	V
Total Capacitance (V _R = 1.0 V, f = 1.0 MHz)	СТ	-	5.0	pF
Reverse Leakage (V _R = 25 V)	I _R	-	1.0	μAdc
Forward Voltage (I _F = 1.0 mAdc)	V _F	-	380	mVdc
Forward Voltage (I _F = 10 mAdc)	V _F	-	500	mVdc
Forward Voltage (I _F = 40 mAdc)	V _F	-	1.0	Vdc



100 T_A = 150°C 125°C 10.001 0.001 0 5.0 10 15 20 25 V_R, REVERSE VOLTAGE (VOLTS)

Figure 1. Typical Forward Voltage

Figure 2. Reverse Current versus Reverse Voltage

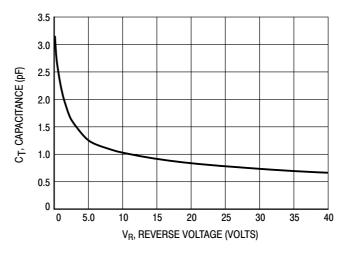
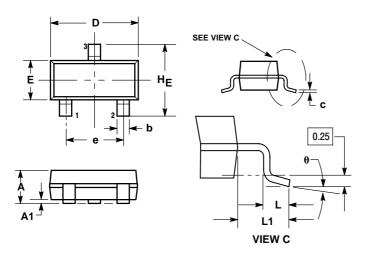


Figure 3. Typical Capacitance

BAS40LT1

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AN



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

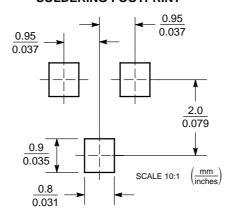
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 8:

PIN 1. ANODE

- 2. NO CONNECTION
- 3. CATHODE

SOLDERING FOOTPRINT*



*For additional information on our Pb—Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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